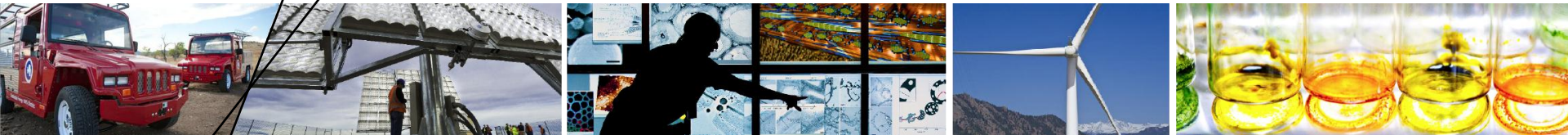


5-parameter PV Module Model



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Outline

- 1. Quick review of single diode model**
- 2. Automated method for estimating model parameters from STC measurements**
- 3. Overview of CEC module database and related processes**

Overview

- **Basic 5 parameter single diode model designed to predict module performance using only data points typically supplied on a manufacturer datasheet**
 - V_{mp} , I_{mp} , V_{oc} , I_{sc} , α , β , γ , N
- **Many implementations: SAM, PVsyst, PV_LIB, ...**
- **Many variations: 6/7 parameters, 2 diodes, ...**
- **Evaluations by Boyd, et al (2011) indicate model predicts within 6% RMS for c-Si, mc-Si, less accurate for thin-film CIS and a-Si.**

Model Equations

- Standard 5 parameter (a , I_L , I_o , R_s , R_{sh}) diode equation:

$$I = I_L - I_o \left(\exp \left[\frac{V + IR_s}{a} \right] - 1 \right) - \frac{V + IR_s}{R_{sh}}$$

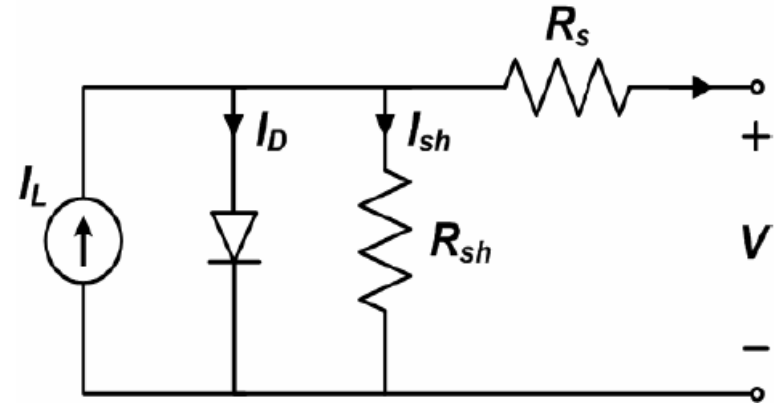
- Translation of parameters to operating conditions:

$$\frac{a}{a_{STC}} = \frac{T_c}{T_{c,STC}}$$

$$\frac{I_o}{I_{o,STC}} = \left[\frac{T_c}{T_{c,STC}} \right]^3 \exp \left[\frac{1}{k} \left(\frac{E_g}{T} \Big|_{T_{c,STC}} - \frac{E_g}{T} \Big|_{T_c} \right) \right]$$

$$\frac{E_g}{E_{g,ref}} = 1 - 0.0002677(T_c - T_{c,STC}) \quad \text{and} \quad E_{g,ref} = 1.121 \text{ eV}$$

$$I_L = \frac{S}{S_{STC}} \frac{M}{M_{STC}} [I_{L,STC} + \alpha(T_c - T_{c,STC})]$$



Variations

- **Observed that modeled max power temp coeff did not always match measured**

- “Adjust” parameter added to tweak $\alpha_{I_{sc}}$, $\beta_{V_{oc}}$ temp coeffs until $\gamma_{modeled} = \gamma_{measured}$

- **δ parameter to add temperature dependence to R_s**

$$R_s = R_{s,STC} \exp\left(\delta(T - T_{ref})\right)$$

- **m parameter to account for nonlinearity in saturation current**

- Need data at different irradiance levels, i.e. P_{max} at 200 W/m²

- $$\frac{I_o}{I_{o,STC}} = \left[\frac{S}{S_{STC}}\right]^m \left[\frac{T_C}{T_{C,STC}}\right]^3 \exp\left[\frac{1}{k} \left(\frac{E_g}{T}\Big|_{T_{C,STC}} - \frac{E_g}{T}\Big|_{T_C}\right)\right]$$

- **PVsyst model adds a recombination current for amorphous modules**

Generating Parameters (SAM impl.)

- Details of method in ref. Dobos, 2012.
- 6 eq., 6 unk.: a , I_L , I_o , R_s , R_{sh} , Adj
 1. Short circuit
 2. Open circuit
 3. Maximum power point
 4. Derivative of MPP
 5. Temp coeff of Voc
 6. Gamma measured = Gamma predicted
- **Multidimensional Newton-Raphson solver implemented in C++ to solve 6 equations 6 unknowns for the model parameters given STC conditions**
- **6th equation for Adjust requires estimation of model-predicted gamma**
 - This is a 2 equation 2 unknown subproblem that is solved with a nested Newton-Raphson implementation

CEC Performance Model with User Entered Specifications

General Information

Module description: Generic polycrystalline silicon module

Cell type: multiSi

Module area: 1.3 m²

Nominal operating cell temperature: 46 °C

Electrical Specifications

Maximum power point voltage (Vmp): 30 V

Maximum power point current (Imp): 6 A

Open circuit voltage (Voc): 37 V

Short circuit current (Isc): 7 A

Temperature coefficient of Voc: -0.11 V/°C

Temperature coefficient of Isc: 0.004 A/°C

Temperature coefficient of max. power point: -0.41 %/°C

Number of cells in series: 60

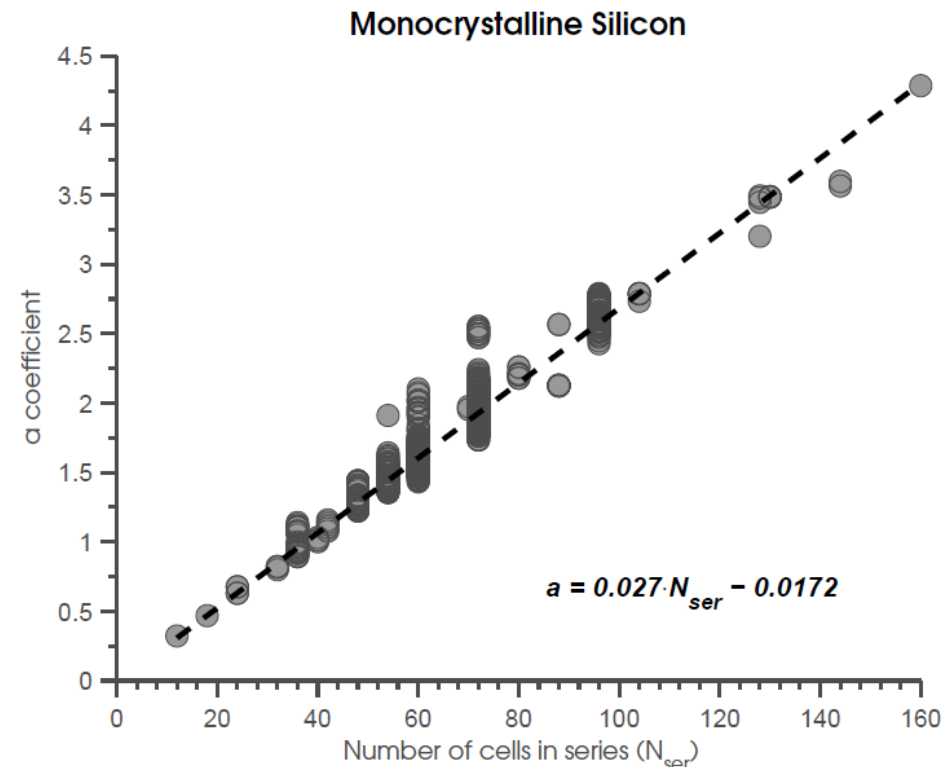
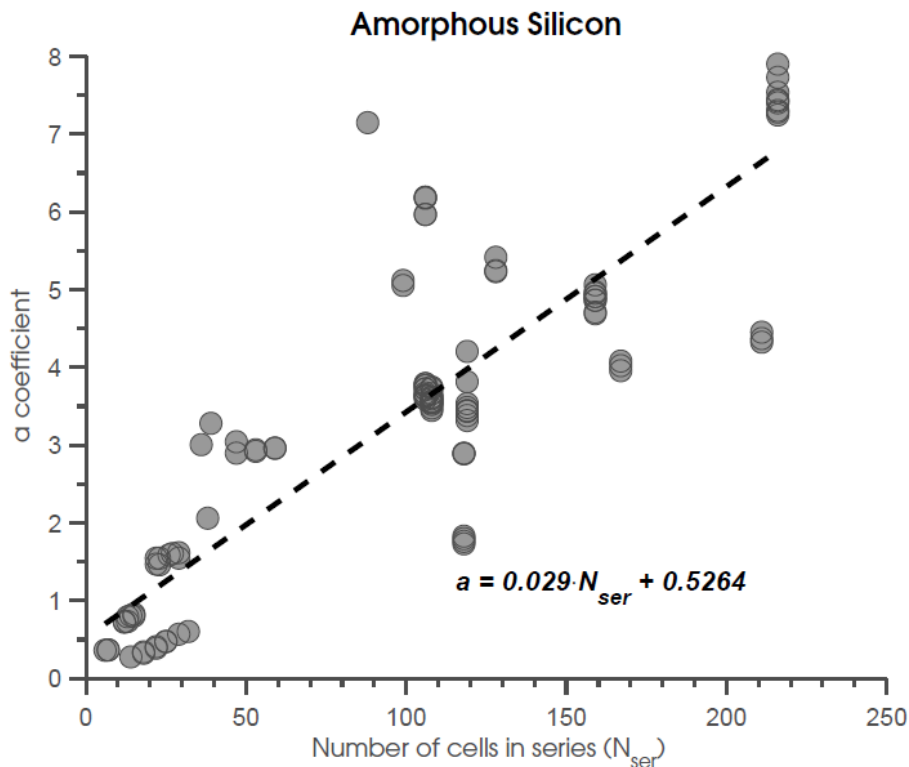
Mounting Configuration

Standoff height: Ground or rack mounted

Approximate installation height: One story building height or lower

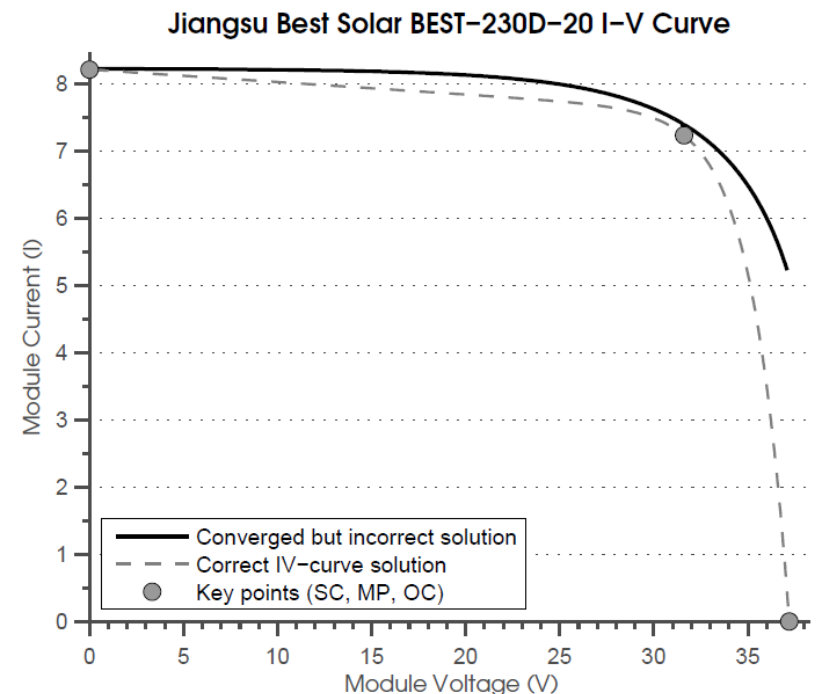
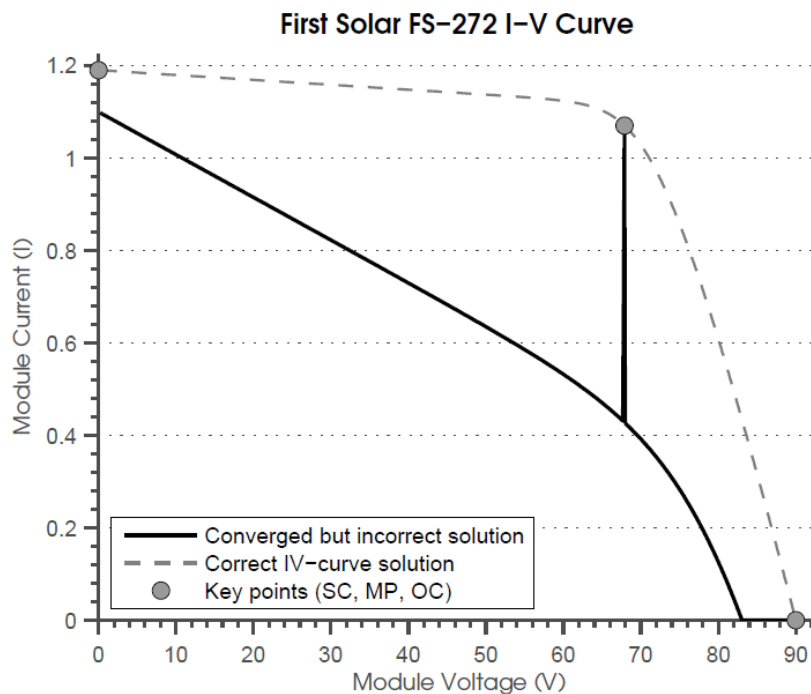
Guess Values

- Method very sensitive to guess values – frequently fails
- Improved convergence with “better” guess values
 - Linear regressions predict resistances and diode factor from module STC parameters, number of cells, technology type. Plots below for modified nonideality factor **a**
 - Solver run across all modules in database, and regressions calculated from those that converged.



Checking Parameters

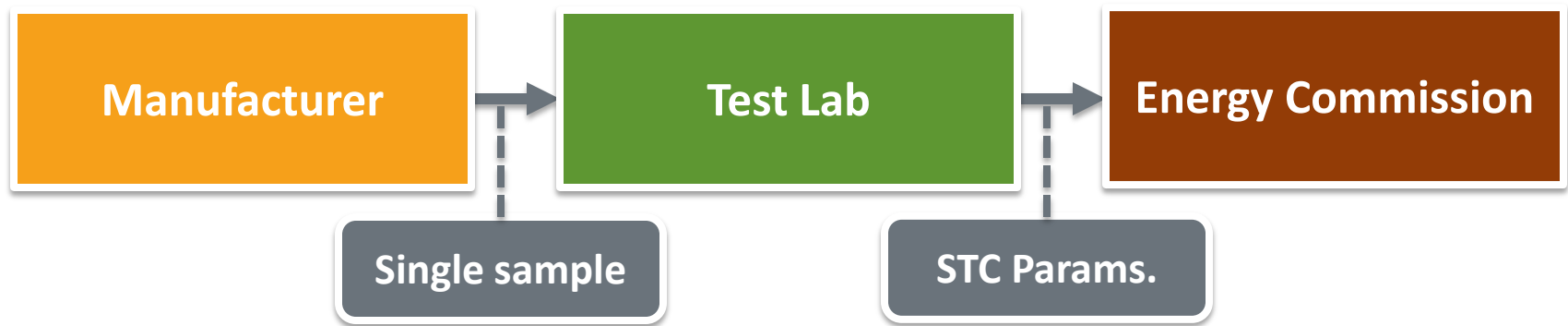
- **Method may converge and yield clearly invalid parameters: sanity checks required**
 - Curve-predicted P_{mp} must be within tolerance of specified P_{mp}
 - Curve-predicted current at V_{oc} must be within tolerance of zero
 - Derivative of IV curve must always be negative
- **If invalid solution found, try again with adjusted guesses.**



CEC Database

- **Developed in support of California’s residential NSHP program**
- **Used to estimate incentive amounts based on projected system performance**
- **Currently over 10000 modules in database, updated several times each year**
- **Since it is a residential program, database not heavily used or originally “intended” for thin-film or amorphous modules – however manufacturers would like to be listed in the database for a variety of reasons**

CEC General Process



- **Manufacturer sends single sample of a module to a test lab holding ILAC accreditation, implementing procedures IEC 61215 and 61646 particularly**
 - Weakness: nobody double checks that accreditations are valid and up to date
- **UL, Intertech, TUV, account for approximately 85% of data in database**
- **Test lab then reports results to CEC per manufacturer's request**
- **CEC receives:**
 - Vmp, Imp, Voc, Isc, Pmp @ STC
 - NOCT @ 800 W/m²
 - 5 measured temperature coefficients: bVoc, bVmp, alsc, almp, Gamma
 - Pmp @ 200 W/m² – data quality issues here, not included in public database

CEC Processes (cont)

- **Data may have “scaled” parameters for modules within 5-10 W of each other.(i.e. one test for a 200 W module, and the 195 W variant does not have independent test data)**
 - Many of the 10000+ modules in DB don't have actual measurements
 - Somewhat “squishy” as to which modules require separate testing
- **NOCT and temp coeffs: these values could be from one set of measurements on a module “family”**
- **Currently KEMA processes incoming data, performs basic screening/cleanup, sends monthly report to the CEC, CEC generates model parameters, updates database**
- **CEC does not receive actual IV curve data**
- **Single sample of manufacturer's choice**
 - Can pick “best” module, can resubmit retested modules to CEC later – no fixed rules on this process

Conclusions

- **Limitations**

- Prediction errors for thin-film and amorphous modules higher than c-Si
- Single test sample to characterize a module

- **Successes**

- Exceptionally large database coverage of up-to-date modules
- Minimum set of input data can reduce modeling errors due to user errors and improves access: can be used from datasheet parameters
- Analytical IV curve representation suitable for module and string mismatch modeling

- **Future**

- Better treatment of nonlinearities with respect to irradiance typically require additional test data to estimate model parameters
- Other extensions/improvements not described here? Suggestions welcome.

References

- **Boyd, M.T.; Klein, S.A.; Reindl, D.T.; Dougherty, B.P.; Evaluation and Validation of Equivalent Circuit Photovoltaic Solar Cell Performance Models. J. Solar Energy Engineering, 133(2), 2011.**
- **DeSoto, W.; Klein, S.A.; Beckman, W.A.; Improvement and Validation of a Model for Photovoltaic Array Performance. Solar Energy, 80(1), 2006.**
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